

NPN Silicon Epitaxial Planar Transistor

KTC4076W

FEATURES

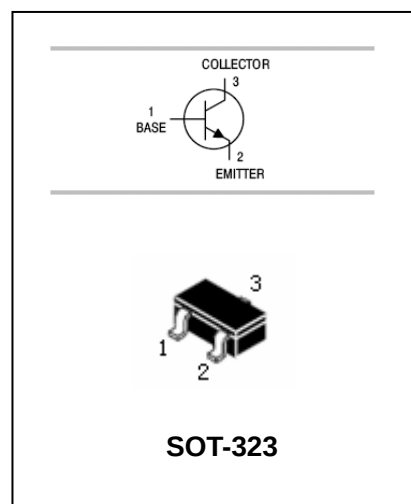
- Excellent H_{FE} Linearity.
- Complementary to KTA2015
- Power dissipation. ($P_C=100\text{mW}$)



Lead-free

APPLICATIONS

- General purpose and switching application.



ORDERING INFORMATION

Type No.	Marking	Package Code
KTC4076W	WOW/Y	SOT-323

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	500	mA
P_C	Collector Dissipation	100	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^\circ\text{C}$

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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=35V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V, I_C=100mA$	70		240	
		$V_{CE}=6V, I_C=400mA$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$		0.1	0.25	V
Transition frequency	f_T	$V_{CE}=6V, I_C=20mA$				MHz
Collector output capacitance	C_{ob}	$V_{CB}=6V, I_E=0mA$ $f=1MHz$		7.0		pF

CLASSIFICATION OF $h_{FE(1)}$

Range	O	Y
Marking	70-140	120-240

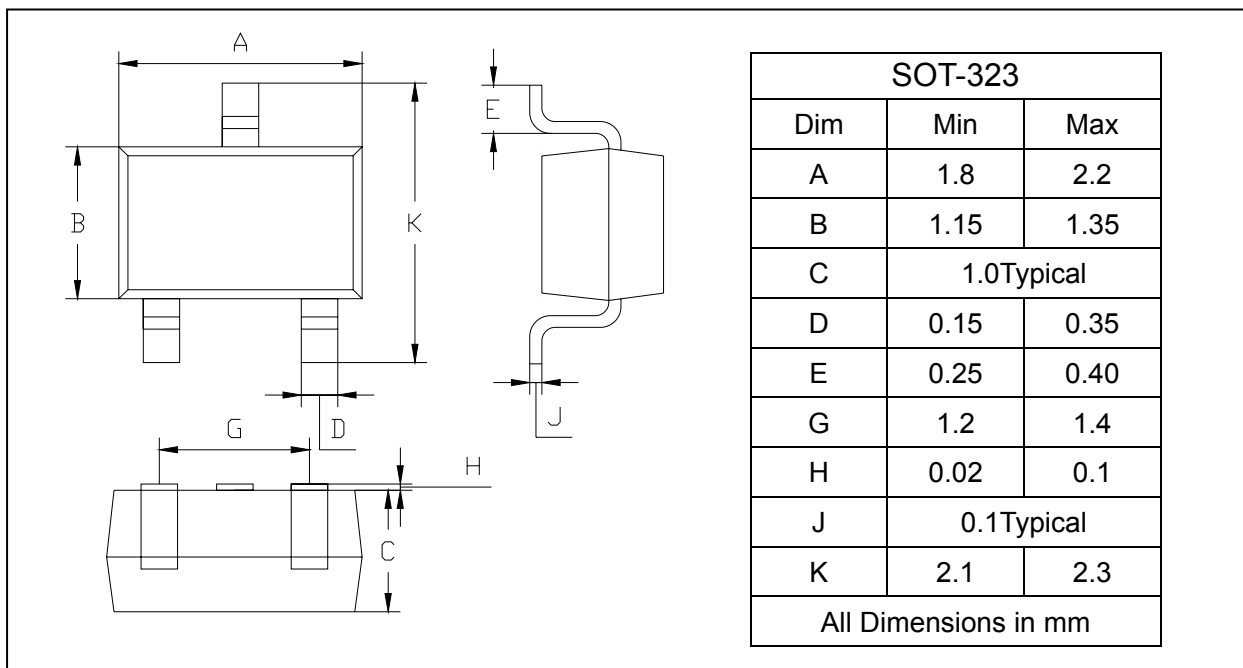
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PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



PACKAGE INFORMATION

Device	Package	Shipping
KTC4076W	SOT-323	3000/Tape&Reel